

SD100-11-21-221

Silicon Photodiode

The SD100-11-21-221 is 5mm² silicon PIN photodiode, packaged in a hermetic TO-5 metal package. The device is suitable for high speed and high sensitivity applications with the spectral range from 350 to 1100nm. It is ideal ideal for visible and near IR applications, including such AC applications as detection of pulsed LASER sources, LEDs, or chopped light.

Applications

| Pulse Detectors |
|------------------------|
| Optical Communications |
| Bar Code Readers |
| Optical Remote Control |
| Medical Equipment |
| High Speed Photometry |

Features

| High Speed Response |
|---------------------|
| Low Capacitance |
| Low Dark Current |
| Wide Dynamic Range |
| High Responsivity |





Absolute Maximum Ratings

| Parameter | Symbol | Min | Max | Unit |
|-----------------------|---------------------|-----|------|------|
| Reverse Voltage | $V_{_{\mathrm{R}}}$ | - | 50 | V |
| Operating Temperature | T_OP | -40 | +125 | °C |
| Storage Temperature | T_{stg} | -55 | +150 | °C |

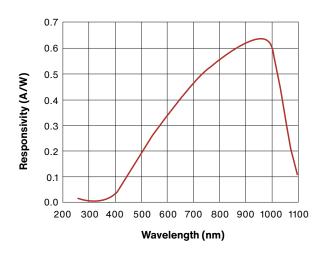
Package TO-5

Typical Electro-Optical Specifications at T_A=23 °C

| Parameter | Test Conditions | Symbol | Min | Тур | Max | Unit |
|----------------------------|--------------------------------|---------------------------|------|-----------------------|------|-------|
| Active Area | - | A.A. | - | 5.1 | - | mm² |
| Spectral Range | - | Δλ | 350 | - | 1100 | nm |
| Responsivity | λ =633nm, V_R =0 V | R_{λ} | 0.32 | 0.36 | - | A/W |
| | λ=900nm, V _R =0V | R_{λ} | 0.50 | 0.55 | - | A/W |
| Junction Capacitance | V _R =0V, F=1MHz | C _J | - | 87 | - | pF |
| | V _R =5V, F=1MHz | $\mathbf{C}_{\mathtt{J}}$ | - | 18 | - | pF |
| Shunt Resistance | V _R =10mV | R _{SH} | 300 | - | - | ΜΩ |
| Dark Current | V _R =5V | I _D | - | 1.6 | 6.4 | nA |
| Noise Equivalent Power | V _R =5V@ λ=950nm | NEP | - | 4.0x10 ⁻¹⁴ | - | W/√HZ |
| Response Time* | $R_L=50\Omega$, $V_R=0V$ | t _R | - | 190 | - | ns |
| | $R_L = 50\Omega$, $V_R = 10V$ | t _R | - | 13 | - | ns |
| Spectral Application Range | Spot Scan | λ | 350 | - | 1100 | nm |

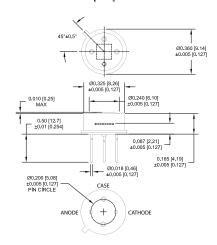
^{*}Response time of 10% to 90% is specified at 660nm wavelength light.

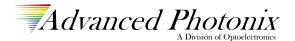
Spectral Response



Mechanical Specifications

Units are in inches [mm]







Care and handling instructions

Your optoelectronic components are packaged and shipped in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

Care must be taken to avoid exposure to high ambient light levels, particularly from tungsten sources or sunlight.

- These components can be rendered inoperable
 if dropped or sharply jarred. The wire bonds are
 delicate and can become separated from the
 bonding pads when the component is dropped or
 otherwise receives a sharp physical blow.
- Most windows on photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.
- Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance. Maintain a non-condensing environment for optimum performance and lifetime.
- All devices are considered ESD sensitive.
 The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.
- Photodiode packages and/or operation may be impaired if exposed to CHLOROETHENE, THINNER, ACETONE, TRICHLOROETHYLENE or any harsh chemicals.
- **Legal Disclaimer**

Information in this data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.



Most of our standard catalog products are RoHS Compliant. Please contact us for details.

- optoelectronic components in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.
- The leads on the photodiode SHOULD NOT BE FORMED. If your application requires lead spacing modification, please contact Advanced Photonix Applications group at Techsupport@advancedphotonix.com before forming a product's leads. Product warranties could be voided.
- Most devices are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:
 - Soldering Iron: Soldering 30 W or less
 - Temperature at tip of iron 300°C or lower.
 - Dip Soldering: Bath Temperature: 260±5°C.
 - Immersion Time: within 5 Sec.
 - Soldering Time: within 3 Sec.
 - Vapor Phase Soldering, Reflow Soldering: DO NOT USE

